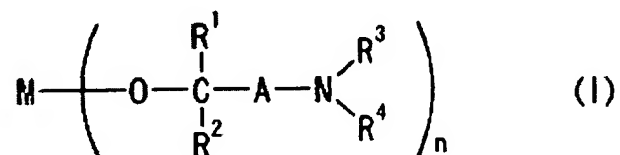


## ABSTRACT OF THE DISCLOSURE

An alkoxide compound of formula (I) suitable as a material for thin film formation used in thin film formation involving vaporization of a material such as CVD, a material for thin film formation including the alkoxide compound, and a process for thin film formation using the material. The process includes vaporizing the material for thin film formation, introducing the resulting vapor containing the alkoxide compound, onto a substrate, and causing the vapor to decompose and/or chemically react to form a thin film on the substrate.



wherein one of  $\text{R}^1$  and  $\text{R}^2$  represents an alkyl group having 1-4 carbon atoms, the other representing a hydrogen atom or an alkyl group having 1-4 carbon atoms;  $\text{R}^3$  and  $\text{R}^4$  each represent an alkyl group having 1-4 carbon atoms; A represents an alkanediyl group having 1-8 carbon atoms; M represents a silicon atom or a hafnium atom; and n represents 4.